

# MOSFET – Power, Single N-Channel

40 V, 237 A, 1.2 mΩ

## NTMJS1D2N04CL

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- LPAK8 Package, Industry Standard
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter			Value	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage			40	V
V <sub>GS</sub>	Gate-to-Source Voltage			±20	V
I <sub>D</sub>	Continuous Drain Current R <sub>θJC</sub> (Notes 1, 3)	Steady State	T <sub>C</sub> = 25°C	237	A
			T <sub>C</sub> = 100°C	168	
P <sub>D</sub>	Power Dissipation R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 25°C	128	W
			T <sub>C</sub> = 100°C	64	
I <sub>D</sub>	Continuous Drain Current R <sub>θJA</sub> (Notes 1, 2, 3)	Steady State	T <sub>A</sub> = 25°C	41	A
			T <sub>A</sub> = 100°C	29	
P <sub>D</sub>	Power Dissipation R <sub>θJA</sub> (Notes 1, 2)		T <sub>A</sub> = 25°C	3.8	W
			T <sub>A</sub> = 100°C	1.9	
I <sub>DM</sub>	Pulsed Drain Current	T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs		1480	A
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature Range			-55 to +175	°C
I <sub>S</sub>	Source Current (Body Diode)			107	A
E <sub>AS</sub>	Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 19 A)			453	mJ
T <sub>L</sub>	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

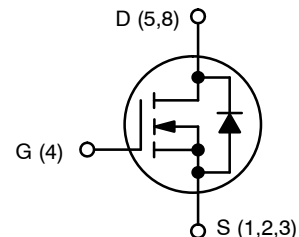
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State	1.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	36	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	1.2 mΩ @ 10 V	237 A
	1.8 mΩ @ 4.5 V	

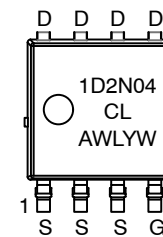


LPAK8  
CASE 760AA



N-CHANNEL MOSFET

### MARKING DIAGRAM



1D2N04CL = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NTMJS1D2N04CL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40			V
V <sub>(BR)DSS</sub> /T <sub>J</sub>	Drain-to-Source Breakdown Voltage Temperature Coefficient			20		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 40 V			10	μA
					250	
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA

### ON CHARACTERISTICS (Note 6)

V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 170 μA	1.2		2.0	V
V <sub>GS(TH)</sub> /T <sub>J</sub>	Threshold Temperature Coefficient			-5.9		mV/°C
R <sub>DS(on)</sub>	Drain-to-Source On Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A		1.5	1.8	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		1	1.2	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 50 A		190		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V		5600		pF
C <sub>OSS</sub>	Output Capacitance			2600		
C <sub>RSS</sub>	Reverse Transfer Capacitance			70		
Q <sub>G(TOT)</sub>	Total Gate Charge	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		44		nC
Q <sub>G(TOT)</sub>	Total Gate Charge	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		93		nC
Q <sub>G(TH)</sub>	Threshold Gate Charge	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A		9.4		
Q <sub>GS</sub>	Gate-to-Source Charge			17.2		
Q <sub>GD</sub>	Gate-to-Drain Charge			13.6		
V <sub>GP</sub>	Plateau Voltage			3.1		V

### SWITCHING CHARACTERISTICS (Note 7)

t <sub>d(ON)</sub>	Turn-On Delay Time	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V, I <sub>D</sub> = 50 A, R <sub>G</sub> = 2.5 Ω		24		ns
t <sub>r</sub>	Rise Time			72		
t <sub>d(OFF)</sub>	Turn-Off Delay Time			122		
t <sub>f</sub>	Fall Time			116		

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Forward Diode Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 50 A	T <sub>J</sub> = 25°C		0.76	1.2	V
			T <sub>J</sub> = 125°C		0.66		
t <sub>RR</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 50 A		59		ns	
t <sub>a</sub>	Charge Time			29			
t <sub>b</sub>	Discharge Time			30			
Q <sub>RR</sub>	Reverse Recovery Charge			43		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

7. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

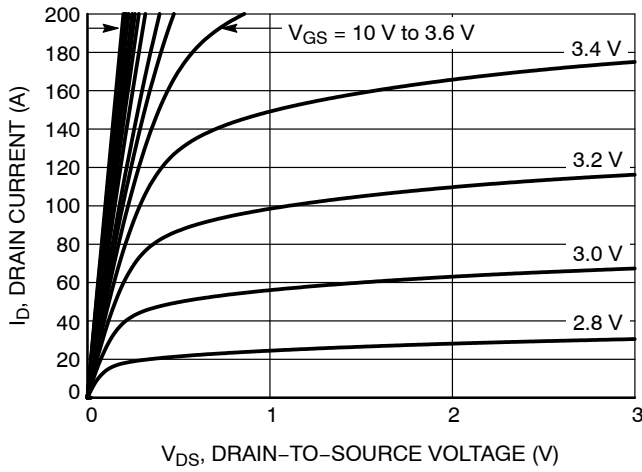


Figure 1. On-Region Characteristics

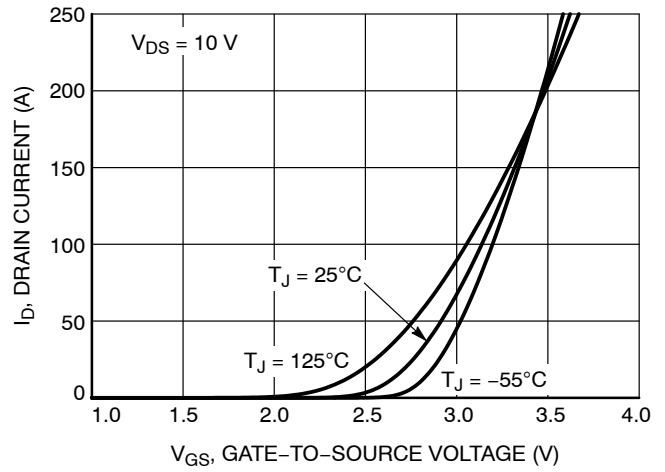


Figure 2. Transfer Characteristics

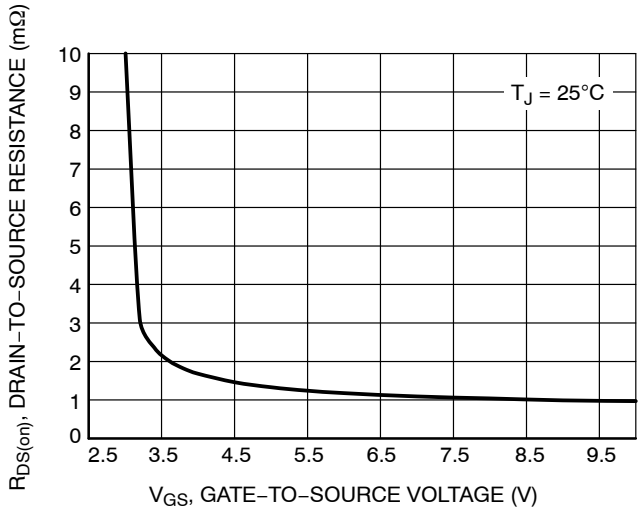


Figure 3. On-Resistance vs. Gate-to-Source Voltage

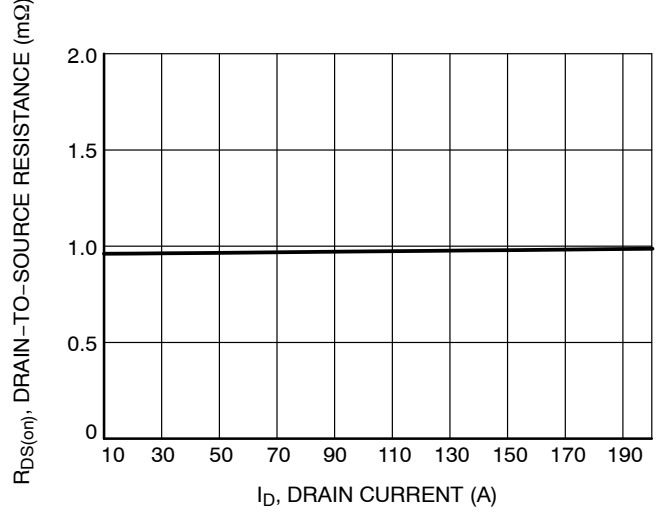


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

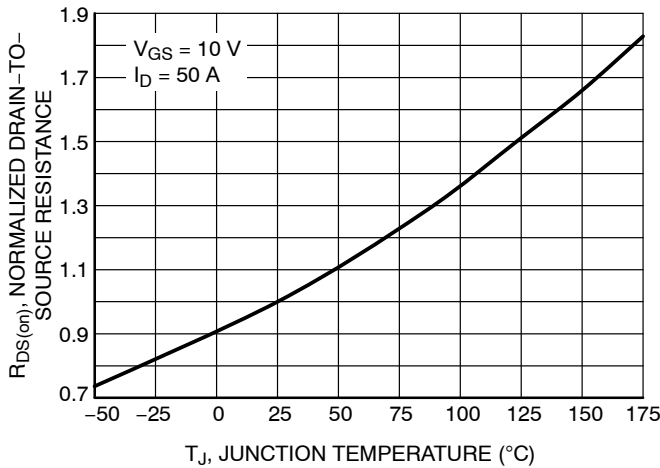


Figure 5. On-Resistance Variation with Temperature

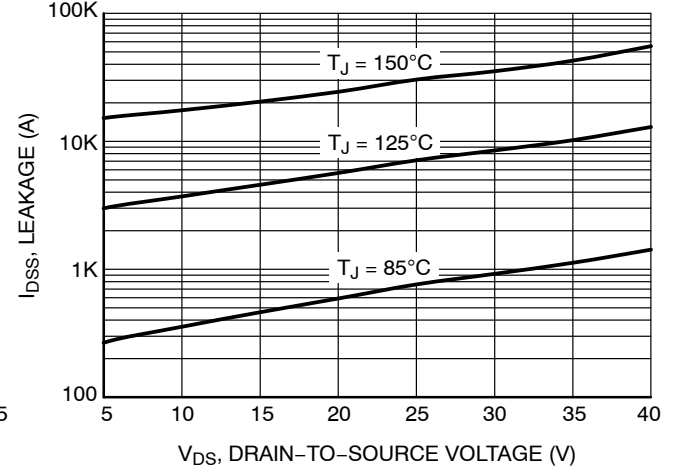


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

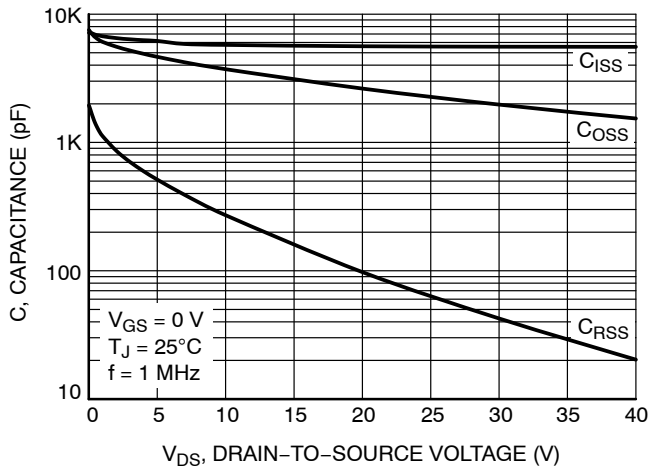


Figure 7. Capacitance Variation

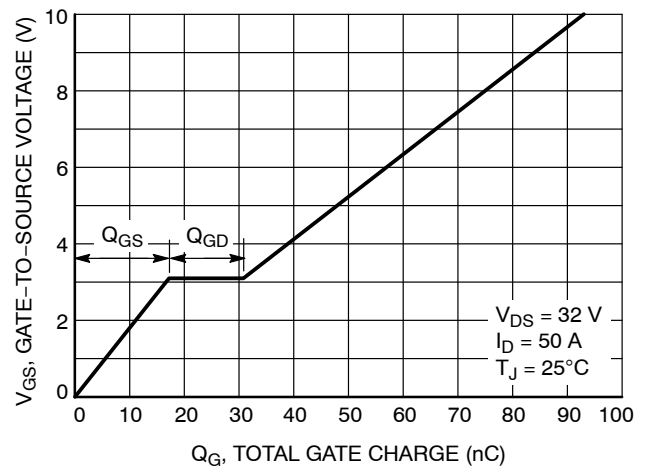


Figure 8. Gate-to-Source Voltage vs. Total Charge

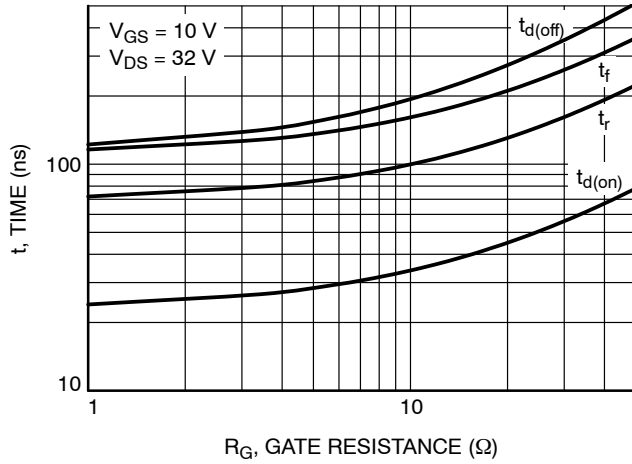


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

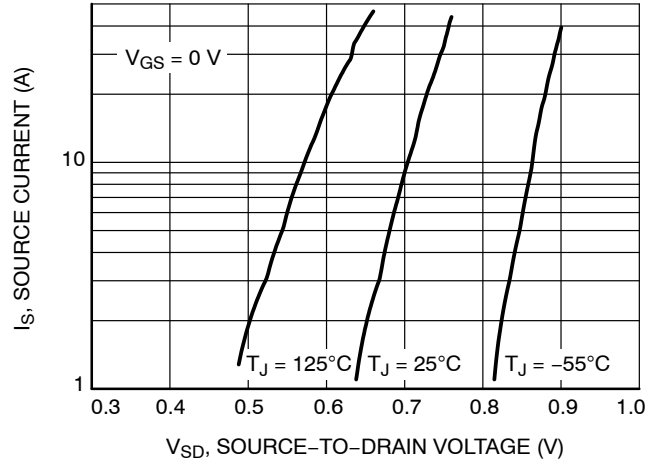


Figure 10. Diode Forward Voltage vs. Current

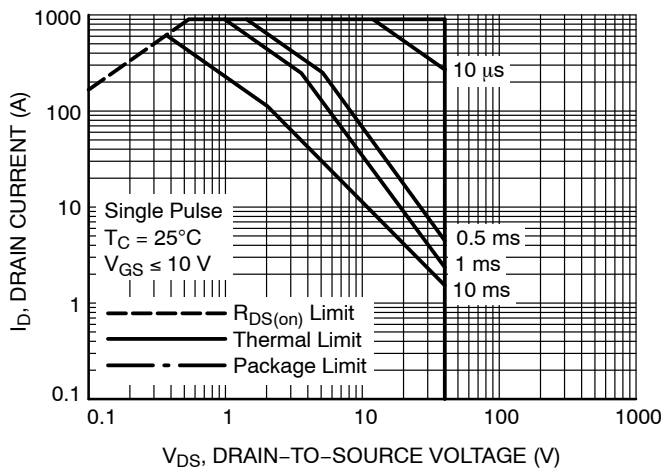


Figure 11. Maximum Rated Forward Biased Safe Operating Area

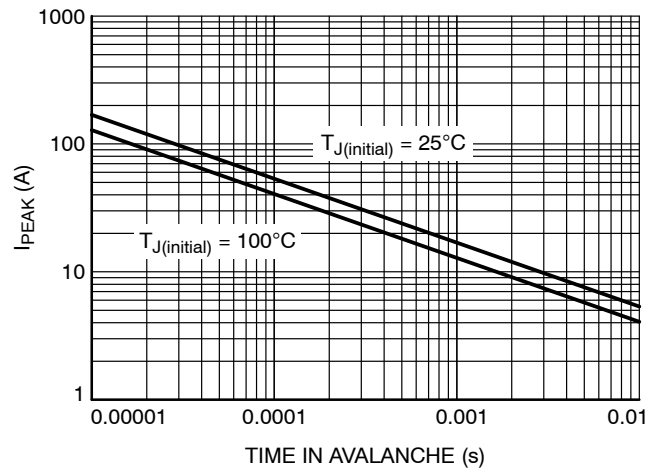


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

# NTMJS1D2N04CL

## TYPICAL CHARACTERISTICS (continued)

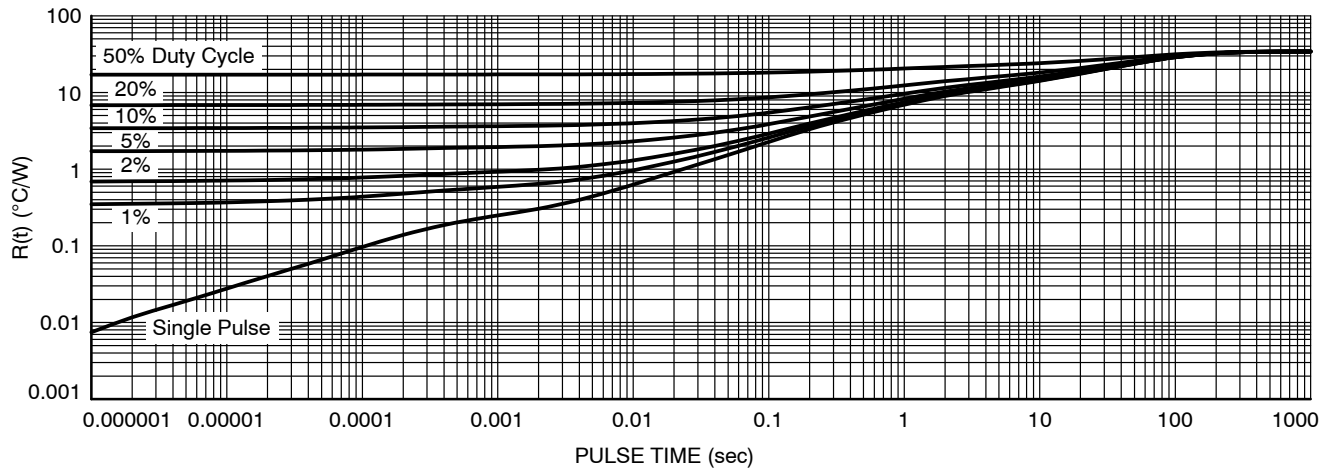


Figure 13. Thermal Characteristics

### DEVICE ORDERING INFORMATION

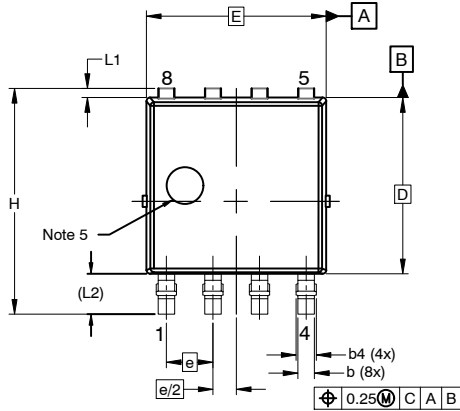
Device	Marking	Package	Shipping <sup>†</sup>
NTMJS1D2N04CLTWG	1D2N04 CL	LFPAK8 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

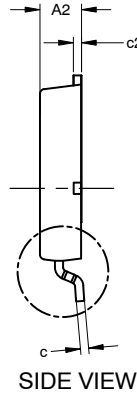


**LFPAK8 4.90x4.80x1.12MM, 1.27P**  
CASE 760AA  
ISSUE D

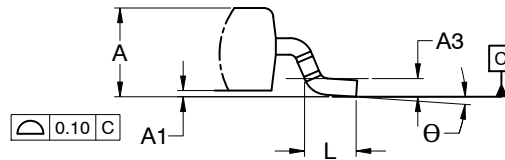
DATE 22 APR 2024



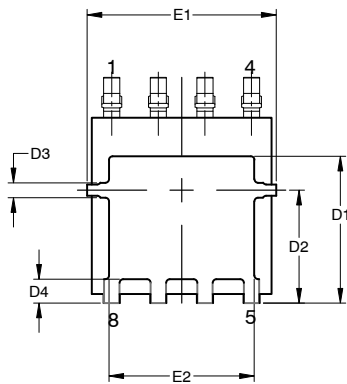
TOP VIEW



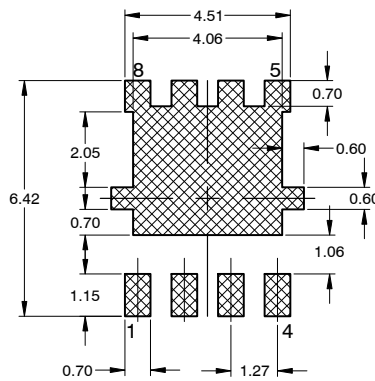
SIDE VIEW



DETAIL 'A'



BOTTOM VIEW



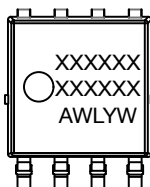
RECOMMENDED LAND PAD

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. OPTIONAL MOLD FEATURE.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 BSC		
b	0.40	0.45	0.50
b4	0.45	0.55	0.65
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.70	4.80	4.90
D1	3.80	4.00	4.20
D2	2.98	3.08	3.18
D3	0.30	0.40	0.50
D4	0.55	0.65	0.75
E	4.80	4.90	5.00
E1	5.05	5.15	5.25
E2	3.91	3.96	4.01
e	1.27 BSC		
e/2	0.635 BSC		
H	6.00	6.15	6.30
L	0.50	0.70	0.90
L1	0.15	0.25	0.35
L2	1.10 REF		
Θ	0°	4°	8°

**GENERIC MARKING DIAGRAM\***



XXXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

\*This information is generic. Please refer to device data sheet for actual part marking. Some products may not follow the Generic Marking.

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